

Norifumi Fujimura

List of Publications by Year in descending order

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164
papers

2,974
citations

257450

24
h-index

189892

50
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164
all docs

164
docs citations

164
times ranked

2462
citing authors

#	ARTICLE	IF	CITATIONS
1	Single-layered assembly of vanadium pentoxide nanowires on graphene for nanowire-based lithography technique. <i>Nanotechnology</i> , 2022, 33, 075602.	2.6	0
2	Metallic Transport in Monolayer and Multilayer Molybdenum Disulfides by Molecular Surface Charge Transfer Doping. <i>ACS Applied Materials & Interfaces</i> , 2022, , .	8.0	3
3	Strong Photoluminescence Enhancement from Bilayer Molybdenum Disulfide via the Combination of UV Irradiation and Superacid Molecular Treatment. <i>Applied Sciences (Switzerland)</i> , 2021, 11, 3530.	2.5	2
4	Ultralarge Photoluminescence Enhancement of Monolayer Molybdenum Disulfide by Spontaneous Superacid Nanolayer Formation. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 25280-25289.	8.0	8
5	Time-Dependent Imprint in $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ Ferroelectric Thin Films. <i>Advanced Electronic Materials</i> , 2021, 7, 2100151.	5.1	18
6	Correlation between photoluminescence and antiferromagnetic spin order in strongly correlated YMnO_3 ferroelectric epitaxial thin film. <i>AIP Advances</i> , 2021, 11, 075122.	1.3	1
7	Investigation of the wake-up process and time-dependent imprint of $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ film through the direct piezoelectric response. <i>Applied Physics Letters</i> , 2021, 119, .	3.3	6
8	Functional Hybridization of Molecules with 2D Semiconducting Materials. <i>Zairyo/Journal of the Society of Materials Science, Japan</i> , 2021, 70, 721-726.	0.2	0
9	Photoactivation of Strong Photoluminescence in Superacid-Treated Monolayer Molybdenum Disulfide. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 36496-36504.	8.0	24
10	Valence states and the magnetism of Eu ions in Eu-doped GaN. <i>Journal of Applied Physics</i> , 2020, 127, 083901.	2.5	5
11	Change in the defect structure of composition controlled single-phase YbFe_2O_4 epitaxial thin films. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SPPB07.	1.5	4
12	Investigation of efficient piezoelectric energy harvesting from impulsive force. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SPPD04.	1.5	6
13	Novel Ferroelectric Gate Field-Effect Transistors (FeFETs); Controlled Polarization-Type FeFETs. <i>Topics in Applied Physics</i> , 2020, , 147-174.	0.8	0
14	Fabrication and Characterization of $(\text{Ba},\text{La})\text{SnO}_3$ Semiconducting Epitaxial Films on (111) and (001) SrTiO_3 Substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1700800.	1.8	2
15	The effects of small amounts of oxygen during deposition on structural changes in sputtered HfO_2 -based films. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SLLB03.	1.5	8
16	Fabrication of chemical composition controlled YbFe_2O_4 epitaxial thin films. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SLLB11.	1.5	1
17	Piezoelectric energy harvesting from AC current-carrying wire. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SLLD10.	1.5	10
18	Electromechanical characteristics of piezoelectric vibration energy harvester with 2-degree-of-freedom system. <i>Applied Physics Letters</i> , 2019, 114, .	3.3	15

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19	Electronic Structure Mosaicity of Monolayer Transition Metal Dichalcogenides by Spontaneous Pattern Formation of Donor Molecules. ACS Applied Materials & Interfaces, 2019, 11, 15922-15926.	8.0	3
20	Time-resolved simulation of the negative capacitance stage emerging at the ferroelectric/semiconductor hetero-junction. AIP Advances, 2019, 9, 025037.	1.3	3
21	Demonstration of high-performance piezoelectric MEMS vibration energy harvester using BiFeO ₃ film with improved electromechanical coupling factor. Sensors and Actuators A: Physical, 2019, 291, 167-173.	4.1	19
22	Saturated and Pinched Ferroelectric Hysteresis Loops in BiFeO ₃ Ceramics. Journal of the Korean Physical Society, 2019, 74, 269-273.	0.7	0
23	Quantitative analysis of the direct piezoelectric response of bismuth ferrite films by scanning probe microscopy. Scientific Reports, 2019, 9, 19727.	3.3	4
24	The effect of crystal distortion and domain structure on piezoelectric properties of BiFeO ₃ thin films. Japanese Journal of Applied Physics, 2018, 57, 11UF07.	1.5	5
25	Investigation of mechanical nonlinear effect in piezoelectric MEMS vibration energy harvesters. Japanese Journal of Applied Physics, 2018, 57, 11UD03.	1.5	9
26	Tuning Transition-Metal Dichalcogenide Field-Effect Transistors by Spontaneous Pattern Formation of an Ultrathin Molecular Dopant Film. ACS Nano, 2018, 12, 10123-10129.	14.6	3
27	Systematic Study of Photoluminescence Enhancement in Monolayer Molybdenum Disulfide by Acid Treatment. Langmuir, 2018, 34, 10243-10249.	3.5	29
28	Reaction of N,N-dimethylformamide and divalent viologen molecule to generate an organic dopant for molybdenum disulfide. AIP Advances, 2018, 8, 055313.	1.3	4
29	Cerium ion doping into self-assembled Ge using three-dimensional dot structure. Journal of Crystal Growth, 2017, 468, 696-700.	1.5	1
30	Strain Dependent Electronic Structure and Band Offset Tuning at Heterointerfaces of A ₂ SnO ₃ (A=Ca, Sr, Ba) / Overlaid 10 T	3.8	19
31	High efficiency piezoelectric MEMS vibrational energy harvesters using (100) oriented BiFeO ₃ films. , 2017, , .		1
32	Growth and ferroelectric properties of La and Al codoped BiFeO ₃ epitaxial films. Journal of Applied Physics, 2017, 121, 174102.	2.5	7
33	Crystallographic polarity effect of ZnO on thin film growth of pentacene. Japanese Journal of Applied Physics, 2017, 56, 04CJ03.	1.5	4
34	Ultrafast dynamics of coherent optical phonon correlated with the antiferromagnetic transition in a hexagonal YMnO ₃ epitaxial film. Applied Physics Letters, 2017, 111, .	3.3	6
35	Large enhancement of positive magnetoresistance by Ce doping in Si epitaxial thin films. Applied Physics Letters, 2016, 109, 112101.	3.3	0
36	Comparative study of ferroelectric (K,Na)NbO ₃ thin films pulsed laser deposition on platinum substrates with different orientation. , 2016, , .		0

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37	Novel chemical vapor deposition process of ZnO films using nonequilibrium N ₂ plasma generated near atmospheric pressure with small amount of O ₂ below 1%. Journal of Applied Physics, 2016, 119, 175302.	2.5	3
38	Al:ZnO top electrodes deposited with various oxygen pressures for ferroelectric (Pb,La)(Zr,Ti)O ₃ capacitors. Electronics Letters, 2016, 52, 230-232.	1.0	5
39	Reliability of the Properties of (Pb,La)(Zr,Ti)O ₃ Capacitors with Non-noble Metal Oxide Electrodes stored in an H ₂ Atmosphere. MRS Advances, 2016, 1, 369-374.	0.9	3
40	Low temperature formation of highly resistive ZnO films using nonequilibrium N ₂ /O ₂ plasma generated near atmospheric pressure. Thin Solid Films, 2016, 616, 415-418.	1.8	1
41	Novel Ferroelectric-Gate Field-Effect Thin Film Transistors (FeTFTs): Controlled Polarization-Type FeTFTs. Topics in Applied Physics, 2016, , 111-138.	0.8	0
42	Fabrication of doped Pb(Zr,Ti)O ₃ capacitors on Pt substrates with different orientations. Electronics Letters, 2016, 52, 1399-1401.	1.0	0
43	Lowering the growth temperature of strongly-correlated YbFe ₂ O ₄ thin films prepared by pulsed laser deposition. Thin Solid Films, 2016, 614, 44-46.	1.8	9
44	The effect of H ₂ distribution in (Pb,La)(Zr,Ti)O ₃ capacitors with conductive oxide electrodes on the degradation of ferroelectric properties. Materials Research Society Symposia Proceedings, 2015, 1729, 93-98.	0.1	0
45	Effects of polarization of polar semiconductor on electrical properties of poly(vinylidene fluoride)/ferroelectric thin film capacitors. Applied Physics Letters, 2015, 106, 101101.	2.5	10
46	Interface energetics and atomic structure of epitaxial La _{1-x} Sr _x CoO ₃ on Nb:SrTiO ₃ . Applied Physics Letters, 2015, 106, .	3.3	8
47	Evaluation of the electronic states in highly Ce doped Si films grown by low temperature molecular beam epitaxy system. Journal of Crystal Growth, 2015, 425, 158-161.	1.5	7
48	Improved reliability properties of (Pb,La)(Zr,Ti)O ₃ ferroelectric capacitors by thin aluminium-doped zinc oxide buffer layer. Electronics Letters, 2014, 50, 799-801.	1.0	4
49	Correlation between the intra-atomic Mn ³⁺ photoluminescence and antiferromagnetic transition in an YMnO ₃ epitaxial film. Applied Physics Express, 2014, 7, 023002.	2.4	10
50	Enhancement of piezoelectric properties of (100)-orientated BiFeO ₃ films on (100)LaNiO ₃ /Si. Japanese Journal of Applied Physics, 2014, 53, 09PA14.	1.5	19
51	Aluminum-doped zinc oxide electrode for robust (Pb,La)(Zr,Ti)O ₃ capacitors: effect of oxide insulator encapsulation and oxide buffer layer. Journal of Materials Science: Materials in Electronics, 2014, 25, 2155-2161.	2.2	5
52	Near-surface structure of polar ZnO surfaces prepared by pulsed laser deposition. Thin Solid Films, 2014, 559, 88-91.	1.8	4
53	Piezoelectric properties of (100) orientated BiFeO ₃ thin films on LaNiO ₃ . Japanese Journal of Applied Physics, 2014, 53, 08NB02.	1.5	11
54	Effect of the annealing temperature of P(VDF/TrFE) thin films on their ferroelectric properties. Journal of the Korean Physical Society, 2013, 62, 1065-1068.	0.7	6

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55	Piezoelectric Vibrational Energy Harvester Using Lead-Free Ferroelectric BiFeO ₃ Films. Applied Physics Express, 2013, 6, 051501.	2.4	37
56	Effects of La substitution for BiFeO ₃ epitaxial thin films. Journal of the Korean Physical Society, 2013, 62, 1069-1072.	0.7	2
57	Orientation Control of ZnO Films Deposited Using Nonequilibrium Atmospheric Pressure N ₂ /O ₂ Plasma. Japanese Journal of Applied Physics, 2013, 52, 01AC03.	1.5	4
58	Development of Piezoelectric MEMS Vibration Energy Harvester Using (100) Oriented BiFeO ₃ Ferroelectric Film. Journal of Physics: Conference Series, 2013, 476, 012007.	0.4	19
59	Enhancement of Direct Piezoelectric Properties of Domain-Engineered (100) BiFeO ₃ Films. Japanese Journal of Applied Physics, 2013, 52, 09KA03.	1.5	10
60	Fabrication and Electric Properties of Ferroelectric-Gate Thin Film Transistors with Nano-Channel. Journal of the Vacuum Society of Japan, 2013, 56, 172-175.	0.3	0
61	Growth temperature and thickness dependences of crystal and micro domain structures of BiFeO ₃ epitaxial films. , 2012, , .		0
62	Electronic Transport in Organic Ferroelectric Gate Field-Effect Transistors with ZnO Channel. Materials Research Society Symposia Proceedings, 2012, 1430, 19.	0.1	1
63	Direct piezoelectric properties of (100) and (111) BiFeO ₃ epitaxial thin films. Applied Physics Letters, 2012, 100, 102901.	3.3	69
64	Control of Crystal Structure of BiFeO ₃ Epitaxial Thin Films by Adjusting Growth Conditions and Piezoelectric Properties. Japanese Journal of Applied Physics, 2012, 51, 09LB04.	1.5	5
65	Effect of Ferroelectric Polarization on Carrier Transport in Controlled Polarization-Type Ferroelectric Gate Field-Effect Transistors with Poly(vinylidene fluoride-tetrafluoroethylene)/ZnO Heterostructure. Japanese Journal of Applied Physics, 2012, 51, 11PB01.	1.5	6
66	Structural analysis and electrical properties of pure Ge ₃ N ₄ dielectric layers formed by an atmospheric-pressure nitrogen plasma. Journal of Applied Physics, 2011, 110, 064103.	2.5	9
67	Surface preparation of ZnO single-crystal substrate for the epitaxial growth of ZnO thin films. Journal of Crystal Growth, 2011, 318, 516-518.	1.5	7
68	Impedance Analysis of Controlled-Polarization-Type Ferroelectric-Gate Thin Film Transistor Using Resistor-Capacitor Lumped Constant Circuit. Japanese Journal of Applied Physics, 2011, 50, 04DD16.	1.5	6
69	Effect of Lattice Misfit Strain on Crystal System and Ferroelectric Property of BiFeO ₃ Epitaxial Thin Films. IOP Conference Series: Materials Science and Engineering, 2011, 18, 092064.	0.6	1
70	Impedance Analysis of Controlled-Polarization-Type Ferroelectric-Gate Thin Film Transistor Using Resistor-Capacitor Lumped Constant Circuit. Japanese Journal of Applied Physics, 2011, 50, 04DD16.	1.5	14
71	Ce-Induced Reconstruction of Si(001) Surface Structures. Japanese Journal of Applied Physics, 2011, 50, 065701.	1.5	2
72	The Difference of Surface Treatment Method for ZnO Single Crystals and the Epitaxial Growth Process Occurred by the Difference in the Surface Polarity. Zairyo/Journal of the Society of Materials Science, Japan, 2011, 60, 983-987.	0.2	0

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73	Growth process observation of homoepitaxial ZnO thin films using optical emission spectra during pulsed laser deposition. <i>Thin Solid Films</i> , 2010, 518, 2971-2974.	1.8	8
74	Analysis of carrier modulation in channel of ferroelectric-gate transistors having polar semiconductor. <i>Thin Solid Films</i> , 2010, 518, 3026-3029.	1.8	14
75	Ferroelectric Properties of Magnetoferroelectric YMnO_3 Epitaxial Films at around the Neel Temperature. <i>Key Engineering Materials</i> , 2010, 445, 144-147.	0.4	1
76	The effects of aluminum doping for the magnetotransport property of Si:Ce thin films. <i>Journal of Applied Physics</i> , 2010, 107, 09C308.	2.5	4
77	Electron transport properties of $\text{Zn}_{0.88}\text{Mn}_{0.12}\text{O}$ modulation-doped heterostructures. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 1760.	1.3	6
78	Magnetic Properties of Uniformly Ce-Doped Si Thin Films with n-Type Conduction. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 033003.	1.5	7
79	Polarization Switching Behavior of YMnO_3 Thin Film at around Magnetic Phase Transition Temperature. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 09KB05.	1.5	12
80	Contribution of s-d exchange interaction to magnetoresistance of ZnO-based heterostructures with a magnetic barrier. <i>Physical Review B</i> , 2009, 80, .	3.2	10
81	Dielectric properties of ferroelectric/DMS heterointerface using YMnO_3 and Ce doped Si. <i>Applied Surface Science</i> , 2008, 254, 6218-6221.	6.1	5
82	Effects of spontaneous and piezoelectric polarizations on carrier confinement at the $\text{Zn}_{0.88}\text{Mn}_{0.12}\text{O}/\text{ZnO}$ interface. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 3107-3109.	0.8	3
83	Electro-optic property of ZnO:Mn epitaxial films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 3110-3112.	0.8	1
84	Influence of antiferromagnetic exchange interaction on magnetic properties of ZnMnO thin films grown pseudomorphically on ZnO (0001Å) single-crystal substrates. <i>Journal of Applied Physics</i> , 2008, 103, .	2.5	33
85	Magnetic and dielectric properties of $\text{Yb}(\text{Mn}_{1-x}\text{Al}_x)\text{O}_3$ thin films. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2008, 55, 1056-1060.	3.0	2
86	$\text{CaBi}_4\text{Ti}_4\text{O}_{15}$ thin film deposition on electroplated Platinum substrates using a sol-gel method. <i>Materials Research Society Symposia Proceedings</i> , 2008, 1113, 1.	0.1	0
87	Electrical Characteristics of Controlled-Polarization-Type Ferroelectric-Gate Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 8874.	1.5	35
88	Spin-dependent transport in a $\text{ZnMnO}\cdot\text{ZnO}$ heterostructure. <i>Journal of Applied Physics</i> , 2008, 103, 07D124.	2.5	7
89	Influence of antiferromagnetic ordering on ferroelectric polarization switching of YMnO_3 epitaxial thin films. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2007, 54, 2641-2644.	3.0	6
90	The comparison of the growth models of silicon nitride ultrathin films fabricated using atmospheric pressure plasma and radio frequency plasma. <i>Journal of Applied Physics</i> , 2007, 101, 023513.	2.5	6

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91	Magnetic frustration behavior of ferroelectric ferromagnet YbMnO ₃ epitaxial films. Journal of Applied Physics, 2007, 101, 09M107.	2.5	12
92	Multiferroic behaviour of YMnO ₃ and YbMnO ₃ epitaxial films. Philosophical Magazine Letters, 2007, 87, 193-201.	1.2	20
93	Influence of Antiferromagnetic Ordering on Ferroelectric Polarization Switching of YMnO ₃ ; Epitaxial Thin Films. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	1
94	Raman scattering studies on multiferroic YMnO ₃ . Journal of Physics Condensed Matter, 2007, 19, 365239.	1.8	55
95	Magnetic properties of low-temperature grown Si:Ce thin films on (001) Si substrate. Journal of Magnetism and Magnetic Materials, 2007, 310, e726-e728.	2.3	10
96	Low temperature growth of Si:Ce thin films with high crystallinity and uniform distribution of Ce grown by solid-source molecular beam epitaxy. Journal of Crystal Growth, 2007, 307, 30-34.	1.5	6
97	Preparation and the magnetic property of ZnMnO thin films on ZnO single crystal substrate. Journal of Magnetism and Magnetic Materials, 2007, 310, e711-e713.	2.3	15
98	Photoluminescence properties peculiar to the Mn-related transition in a lightly alloyed ZnMnO thin film grown by pulsed laser deposition. Applied Physics Letters, 2006, 88, 241908.	3.3	24
99	Growth and Ferromagnetic Properties of Ferroelectric YbMnO ₃ Thin Films. Japanese Journal of Applied Physics, 2006, 45, 7329-7331.	1.5	12
100	Magnetic properties of Er,O-codoped GaAs at low temperature. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 4082-4085.	0.8	0
101	Reaction of Si with excited nitrogen species in pure nitrogen plasma near atmospheric pressure. Thin Solid Films, 2006, 506-507, 423-426.	1.8	16
102	Effect of Additional Oxygen on Formation of Silicon Oxynitride Using Nitrogen Plasma Generated near Atmospheric Pressure. Japanese Journal of Applied Physics, 2006, 45, 9025-9028.	1.5	6
103	Magnetic and Ferroelectric Properties of YMnO ₃ Epitaxial Thin Films. Materials Research Society Symposia Proceedings, 2006, 966, 1.	0.1	4
104	Detailed structural analysis and dielectric properties of silicon nitride film fabricated using pure nitrogen plasma generated near atmospheric pressure. Journal of Applied Physics, 2006, 100, 073710.	2.5	14
105	Electro-optical effect in ZnO:Mn thin films prepared by Xe sputtering. Journal of Applied Physics, 2006, 99, 013509.	2.5	18
106	Interface characteristics of (Zn,Mn)O/ZnO grown on ZnO substrate. Journal of Crystal Growth, 2005, 275, e2211-e2215.	1.5	1
107	Ferromagnetic and dielectric behavior of mn-doped BaCoO ₃ . IEEE Transactions on Magnetics, 2005, 41, 3496-3498.	2.1	13
108	Enhancement of ferromagnetic ordering in dielectric BaFe _{1-x} Zr _x O ₃ (x=0.5-0.8) single-crystal films by pulsed laser-beam deposition. Journal of Applied Physics, 2005, 97, 10M509.	2.5	10

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109	Magnetic properties of low temperature grown Si:Ce thin films on [001] Si substrate by molecular beam epitaxy. , 2005, , .		0
110	Epitaxial growth of CuScO ₂ thin films on sapphire a-plane substrates by pulsed laser deposition. Journal of Applied Physics, 2005, 97, 083535.	2.5	25
111	Ferromagnetic and dielectric behavior of Mn doped BaCoO/sub 3/. , 2005, , .		0
112	Improvement of magnetization and leakage current properties of magnetoelectric BaFeO ₃ thin films by Zr substitution. Applied Physics Letters, 2005, 86, 082902.	3.3	33
113	Formation of Silicon Oxynitride Films with Low Leakage Current Using N ₂ /O ₂ Plasma near Atmospheric Pressure. Japanese Journal of Applied Physics, 2004, 43, 7853-7856.	1.5	7
114	Pulsed-Laser-Deposited YMnO ₃ Epitaxial Films with Square Polarization-Electric Field Hysteresis Loop and Low-Temperature Growth. Japanese Journal of Applied Physics, 2004, 43, 6613-6616.	1.5	31
115	Synthesis of Bi(FexAl _{1-x})O ₃ Thin Films by Pulsed Laser Deposition and Its Structural Characterization. Japanese Journal of Applied Physics, 2004, 43, 6609-6612.	1.5	13
116	The effects of Xe on an rf plasma and growth of ZnO films by rf sputtering. Journal of Applied Physics, 2004, 95, 3923-3927.	2.5	32
117	Optical propagation loss of ZnO films grown on sapphire. Journal of Applied Physics, 2004, 95, 1673-1676.	2.5	7
118	Fabrication of Silicon Nitride Film using Pure Nitrogen Plasma Generated near Atmospheric Pressure for III-V Semiconductor Fabrication. Materials Research Society Symposia Proceedings, 2004, 831, 144.	0.1	0
119	Effect of Oxygen Deficiencies on Magnetic Properties of Epitaxial Grown BaFeO_{3-x} Thin Films on. IEEE Transactions on Magnetics, 2004, 40, 2736-2738.	2.1	35
120	Electro-optic effect in ZnO:Mn thin films. Journal of Alloys and Compounds, 2004, 371, 157-159.	5.5	14
121	Analysis of nitrogen plasma generated by a pulsed plasma system near atmospheric pressure. Journal of Applied Physics, 2004, 96, 6094-6096.	2.5	19
122	Effect of carrier for magnetic and magnetotransport properties of Si:Ce films. Journal of Applied Physics, 2003, 93, 7679-7681.	2.5	14
123	Magnetic properties of highly resistive BaFeO ₃ thin films epitaxially grown on SrTiO ₃ single-crystal substrates. Journal of Applied Physics, 2003, 93, 6993-6995.	2.5	40
124	Investigation of Retention Properties for YMnO ₃ Based Metal/Ferroelectric/Insulator/Semiconductor Capacitors. Materials Research Society Symposia Proceedings, 2003, 784, 971.	0.1	0
125	Investigation of Retention Properties for YMnO ₃ Based Metal/Ferroelectric/Insulator/Semiconductor Capacitors. Materials Research Society Symposia Proceedings, 2003, 786, 971.	0.1	0
126	Ferromagnetic and ferroelectric behaviors of A-site substituted YMnO ₃ -based epitaxial thin films. Journal of Applied Physics, 2003, 93, 6990-6992.	2.5	44

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127	Influence of Schottky and Poole-Frenkel emission on the retention property of YMnO ₃ -based metal/ferroelectric/insulator/semiconductor capacitors. Journal of Applied Physics, 2003, 94, 4036-4041.	2.5	34
128	Magnetic and magnetotransport properties of solid phase epitaxially grown Si:Ce films. Journal of Applied Physics, 2003, 93, 4045-4048.	2.5	14
129	Formation of two-dimensional electron gas and the magnetotransport behavior of ZnMnO/ZnO heterostructure. Journal of Applied Physics, 2003, 93, 7673-7675.	2.5	53
130	Ferroelectric properties of YMnO ₃ epitaxial films for ferroelectric-gate field-effect transistors. Journal of Applied Physics, 2003, 93, 5563-5567.	2.5	105
131	Effect of substitutionally dissolved Ce in Si on the magnetic and electric properties of magnetic semiconductor Si _{1-x} Ce _x films. Applied Physics Letters, 2002, 81, 4023-4025.	3.3	28
132	Electro-Optic Effect in Epitaxial ZnO:Mn Thin Films. Japanese Journal of Applied Physics, 2002, 41, 6916-6918.	1.5	17
133	The Effect of Leakage Current on the Retention Property of YMnO ₃ Based MFIS Capacitor. Integrated Ferroelectrics, 2002, 49, 41-49.	0.7	1
134	The Progress of YMnO ₃ /Y ₂ O ₃ /Si System for a Ferroelectric Gate Field Effect Transistor. Ferroelectrics, 2002, 271, 229-234.	0.6	2
135	Structural, dielectric, and magnetic properties of epitaxially grown BaFeO ₃ thin films on (100) SrTiO ₃ single-crystal substrates. Applied Physics Letters, 2002, 81, 2764-2766.	3.3	89
136	Ce concentration dependence on the magnetic and transport properties of Ce doped Si epitaxial films prepared by molecular beam epitaxy. Journal of Applied Physics, 2002, 91, 7905.	2.5	11
137	Detailed structural analysis of Ce doped Si thin films. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 237-241.	2.7	22
138	Title is missing!. Journal of Sol-Gel Science and Technology, 2000, 19, 589-593.	2.4	11
139	Effect of plasma-induced damage on interfacial reactions of titanium thin films on silicon surfaces. Applied Physics Letters, 2000, 76, 2358-2360.	3.3	3
140	Characterization of ferroelectricity in metal/ferroelectric/insulator/semiconductor structure by pulsed C-V measurement; Ferroelectricity in YMnO ₃ /Y ₂ O ₃ /Si structure. Journal of Applied Physics, 2000, 87, 3444-3449.	2.5	72
141	Ferroelectricity of YMnO ₃ thin films prepared via solution. Applied Physics Letters, 1999, 75, 719-721.	3.3	54
142	YMnO ₃ and YbMnO ₃ Thin Films for fet type FeRam Application. Materials Research Society Symposia Proceedings, 1999, 574, 237.	0.1	3
143	Exotic Doping for Zno Thin Films: Possibility of Monolithic Optical Integrated Circuit. Materials Research Society Symposia Proceedings, 1999, 574, 317.	0.1	9
144	Detailed C-V Analysis for YbMnO ₃ /Y ₂ O ₃ /Si Structure. Materials Research Society Symposia Proceedings, 1999, 574, 359.	0.1	1

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145	Origin of Leakage Current of YMnO ₃ Thin Films Prepared by the Sol-Gel Method. Materials Research Society Symposia Proceedings, 1999, 596, 481.	0.1	3
146	Preparation and Dielectric Properties of YMnO ₃ Ferroelectric Thin Films by the Sol-Gel Method. Journal of Sol-Gel Science and Technology, 1998, 13, 903-908.	2.4	15
147	Ferroelectric properties of c-oriented YMnO ₃ films deposited on Si substrates. Applied Physics Letters, 1998, 73, 414-416.	3.3	60
148	Microstructure and Dielectric Properties of YMnO ₃ Thin Films Prepared by Dip-Coating. Journal of the American Ceramic Society, 1998, 81, 1357-1360.	3.8	20
149	Mechanism for ordering in SiGe films with reconstructed surface. Applied Physics Letters, 1997, 71, 1174-1176.	3.3	3
150	Fabrication of YMnO ₃ Films: New Candidate for Non-Volatile Memory Devices. Materials Research Society Symposia Proceedings, 1996, 433, 119.	0.1	0
151	Epitaxially grown YMnO ₃ film: New candidate for nonvolatile memory devices. Applied Physics Letters, 1996, 69, 1011-1013.	3.3	303
152	Growth mechanism of YMnO ₃ film as a new candidate for nonvolatile memory devices. Journal of Applied Physics, 1996, 80, 7084-7088.	2.5	94
153	Epitaxially Grown Ferroelectric Thin Films. Application to Surface Acoustic Device.. Hyomen Kagaku, 1996, 17, 671-675.	0.0	0
154	Orientation control of (Ca,Sr)CuO ₂ thin films. Journal of Applied Physics, 1995, 77, 3805-3811.	2.5	5
155	LiNbO ₃ film with a new epitaxial orientation on cut sapphire. Journal of Applied Physics, 1994, 75, 2169-2176.	2.5	37
156	Control of preferred orientation for ZnOx films: control of self-texture. Journal of Crystal Growth, 1993, 130, 269-279.	1.5	665
157	Structural control of nonequilibrium WSi _{2.6} thin films by external stress. Journal of Applied Physics, 1993, 73, 733-739.	2.5	3
158	Formation of (1120) ZnO Films by Controlling the Selftexture and the Relaxation of Film Stress. Materials Research Society Symposia Proceedings, 1992, 263, 297.	0.1	2
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